

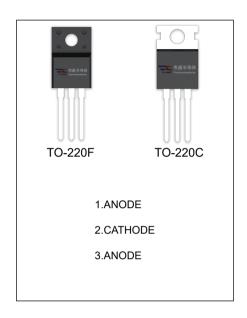
SBD30150SCTB SBDF30150SCTB SCHOTTKY BARRIER RECTIFIER

MAIN CHARACTERISTICS

Io	30 (2×15) A
V_{RRM}	150 V
T _j	150 ℃
$V_{F(typ)}$	0.67V (@Tj=125℃)

FEATURES

- Low Power Loss, High Efficiency
- Guard Ring Die Construction for Transient Protection
- High Current Capability and Low Forward Voltage Drop



MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Cymphol	Parameter	SBD		Unit
Symbol	Parameter		30150SCTB F30150SCTB	
V_{RRM}	Peak repetitive reverse voltage			
V_{RWM}	Working peak reverse voltage		150	
V_R	DC blocking voltage			
V _{R(RMS)}	RMS reverse voltage	105		V
Io	Average rectified output current	30		Α
I _{FSM}	Non-Repetitive peak forward surge current (8.3ms half sine wave)	300		Α
R _{OJc}	Thermal resistance from junction to case ,Tc=25℃	2.0	3.0	°C/W
R _{OJA}	Thermal resistance from junction to ambient	62.5		°C/W
T _j	Junction temperature	150		°C
T _{stg}	Storage temperature	-55~	+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Тур	Max	Unit
Reverse voltage	V _(BR)			I _R =1mA		150	
Reverse current	I _R	V _R =150V	Tj =25℃		10.0	100	uA
			Tj =125℃		5.0		mA
Forward voltage	V _F	I _F =10A	Tj =25℃		0.83		V
			Tj =125℃		0.62		V
		I _F =15A	Tj =25℃		1.05	1.25	V
			Tj =125℃		0.67		V

^{*}Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.



